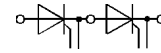


## SKKT 500, SKKH 500

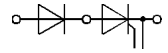
| V <sub>RS</sub> | V <sub>RRM</sub><br>V <sub>DRM</sub> | (dv/dt) <sub>cr</sub> | I <sub>TRMS</sub> (maximum values for continuous operation) |                      |
|-----------------|--------------------------------------|-----------------------|---|----------------------|
|                 |                                      |                       | 920 A   |                      |
|                 |                                      |                       | I <sub>TAV</sub> (sin. 180; T <sub>case</sub> = 80 °C)      |                      |
|                 |                                      |                       | 585 A   |                      |
| 900             | 800                                  | 500                   | <b>SKKT 500/08 D</b>  | <b>SKKH 500/08 D</b> |
| 1300            | 1200                                 | 1000                  | <b>SKKT 500/12 E</b>  | <b>SKKH 500/12 E</b> |
| 1500            | 1400                                 | 1000                  | <b>SKKT 500/14 E</b>  | <b>SKKH 500/14 E</b> |
| 1700            | 1600                                 | 1000                  | <b>SKKT 500/16 E</b>  | <b>SKKH 500/16 E</b> |
| 1900            | 1800                                 | 1000                  | <b>SKKT 500/18 E</b>  | <b>SKKH 500/18 E</b> |

## SEMIPACK® 5 Thyristor / Diode Modules

### SKKT 500 SKKH 500



SKKT



SKKH

| Symbol                            | Conditions   | SKKT 500<br>SKKH 500                 | Units            |
|-----------------------------------|--|--------------------------------------|------------------|
| I <sub>TAV</sub>                  | sin. 180; T <sub>case</sub> = 85 °C  | 540                                  | A                |
| I <sub>D</sub>                    | T <sub>case</sub> = 89 °C  | 500                                  | A                |
| I <sub>RMS</sub>                  | B2/B6  | 665 / 845                            | A                |
|                                   | W1/W3  | P 16/200 F<br>P 16/300 F             | 850 / 3 x 670    |
| I <sub>TSM</sub>                  | T <sub>vj</sub> = 25 °C; 10 ms   | 17 000                               | A                |
|                                   | T <sub>vj</sub> = 130 °C; 10 ms  | 15 000                               | A                |
| i <sup>2</sup> t                  | T <sub>vj</sub> = 25 °C; 8,3 ... 10 ms   | 1 445 000                            | A <sup>2</sup> s |
|                                   | T <sub>vj</sub> = 130 °C; 8,3 ... 10 ms  | 1 125 000                            | A <sup>2</sup> s |
| t <sub>gd</sub>                   | T <sub>vj</sub> = 25 °C I <sub>G</sub> = 1 A<br>di <sub>G</sub> /dt = 1 A/μs                       | 1                                    | μs               |
| t <sub>gr</sub>                   | V <sub>D</sub> = 0,67 · V <sub>DRM</sub>   | 2                                    | μs               |
| (di/dt) <sub>cr</sub>             | T <sub>vj</sub> = 130 °C   | 200                                  | A/μs             |
| t <sub>q</sub>                    | T <sub>vj</sub> = 130 °C   | typ. 100 ... 200                     | μs               |
| I <sub>H</sub>                    | T <sub>vj</sub> = 25 °C; typ./max.   | 150 / 500                            | mA               |
| I <sub>L</sub>                    | T <sub>vj</sub> = 25 °C; R <sub>G</sub> = 33 Ω; typ./max.  | 0,3 / 2                              | A                |
| V <sub>T</sub>                    | T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 1700 A   | max. 1,5                             | V                |
| V <sub>T(TO)</sub>                | T <sub>vj</sub> = 130 °C   | 0,925                                | V                |
| r <sub>T</sub>                    | T <sub>vj</sub> = 130 °C   | 0,27                                 | mΩ               |
| I <sub>DD</sub> ; I <sub>RD</sub> | T <sub>vj</sub> = 130 °C; V <sub>RD</sub> = V <sub>RRM</sub><br>V <sub>DD</sub> = V <sub>DRM</sub> | 100                                  | mA               |
| V <sub>GT</sub>                   | T <sub>vj</sub> = 25 °C; d.c.  | 3                                    | V                |
| I <sub>GT</sub>                   | T <sub>vj</sub> = 25 °C; d.c.  | 200                                  | mA               |
| V <sub>GD</sub>                   | T <sub>vj</sub> = 130 °C; d.c.   | 0,25                                 | V                |
| I <sub>GD</sub>                   | T <sub>vj</sub> = 130 °C; d.c.   | 10                                   | mA               |
| R <sub>thjc</sub>                 | cont.  | } per thyristor /<br>} per module    | 0,062 / 0,031    |
| R <sub>thch</sub>                 | sin. 180   |                                      | 0,065 / 0,0325   |
|                                   | rec. 120   |                                      | 0,070 / 0,035    |
|                                   | T <sub>vj</sub>  |                                      | 0,02 / 0,01      |
|                                   | T <sub>stg</sub>   |                                      | - 40 ... + 130   |
| V <sub>isol</sub>                 | a. c. 50 Hz; r.m.s.; 1 s/1 min   | 3600/3000                            | V~               |
| M <sub>1</sub>                    | to heatsink(M6)  | 5 ± 15 % <sup>1)</sup>               | Nm               |
|                                   | SI units   | 44 ± 15 % <sup>1)</sup>              | lb.in.           |
| M <sub>2</sub>                    | to terminals(M10)  | 12 ± 15 % <sup>2)</sup>              | Nm               |
|                                   | SI units   | 106 ± 15 % <sup>2)</sup>             | lb.in.           |
| a                                 |  | 5 · 9,81                             | m/s <sup>2</sup> |
| w                                 | approx.  | 1420                                 | g                |
| Case                              |  | SKKT 500: A 60 a<br>SKKH 500: A 66 a |                  |

### Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precise metal pressure contacts for high reliability
- UL recognized, file no. E 63 532

### Typical Applications

- AC motor softstarters
- Input converters for AC inverter drives
- DC motor control (e.g. for machine tools)
- Temperature control (e.g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

<sup>1)</sup> See the assembly instructions  
<sup>2)</sup> The screws must be lubricated

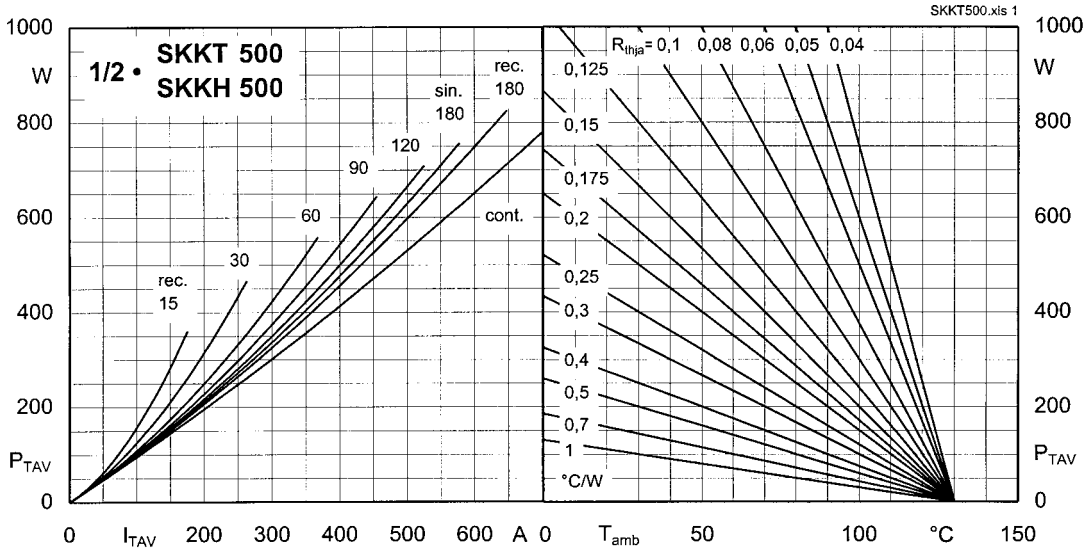


Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

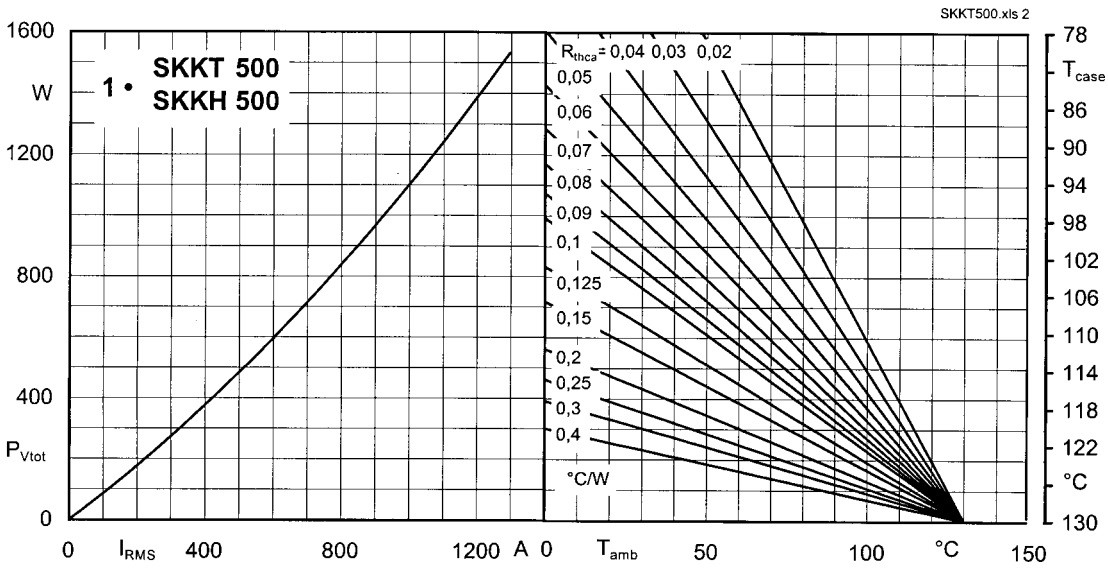


Fig. 2 Power dissipation per module vs. rms current and case temperature

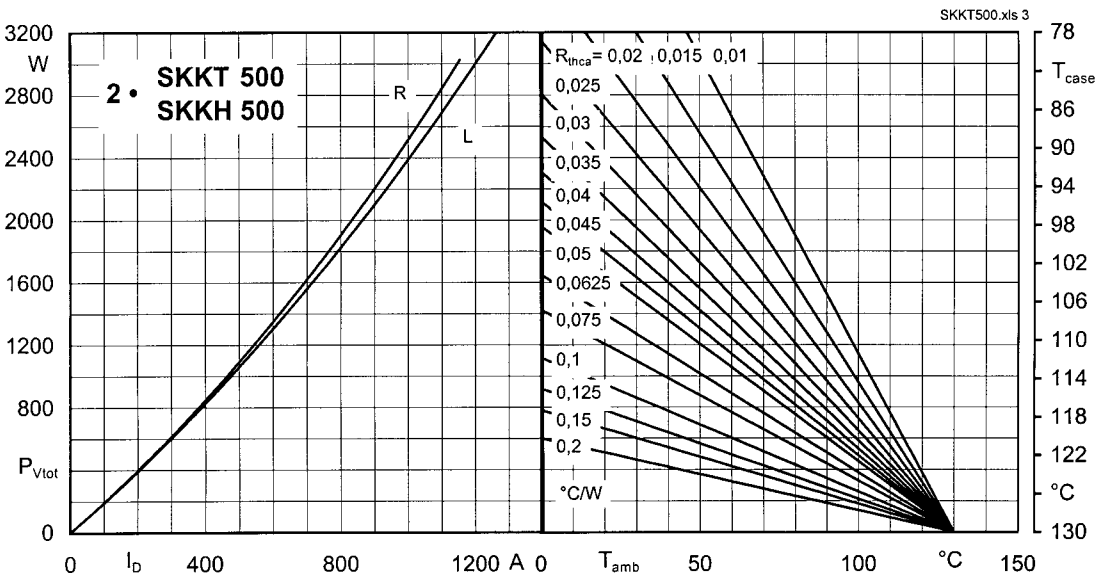


Fig. 3 Power dissipation of two module vs. direct current and case temperature

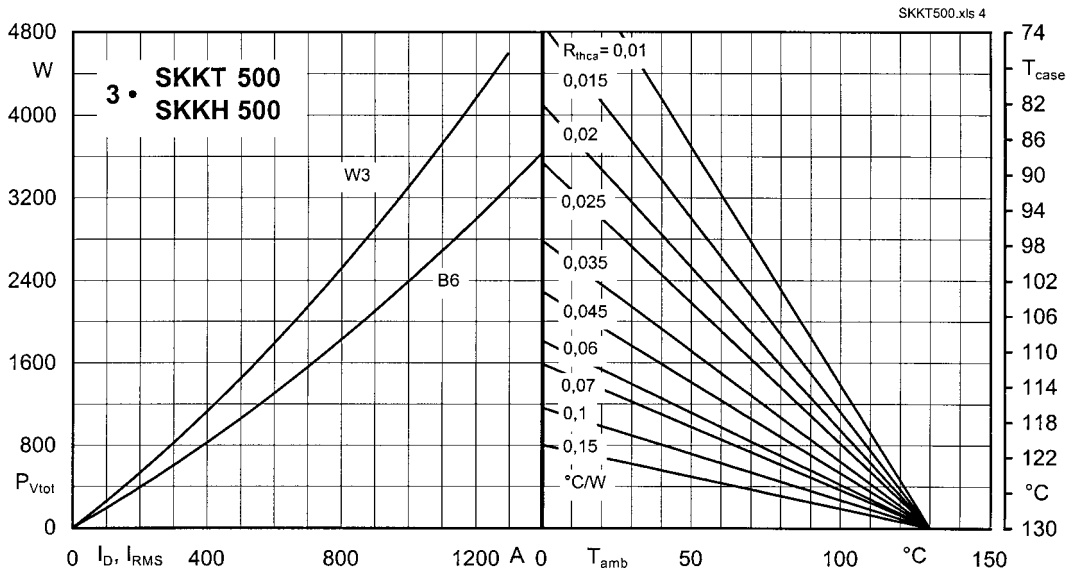


Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

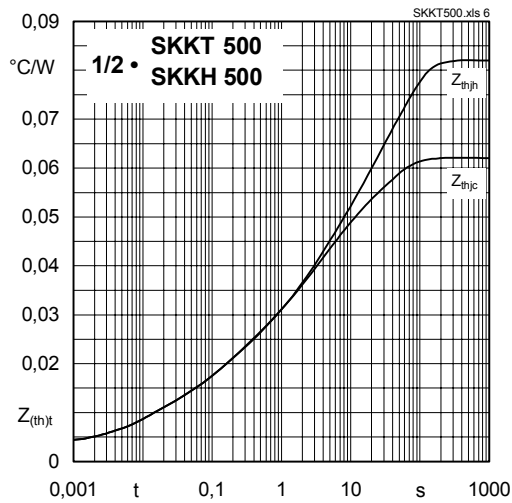


Fig. 6 Transient thermal impedance vs. time

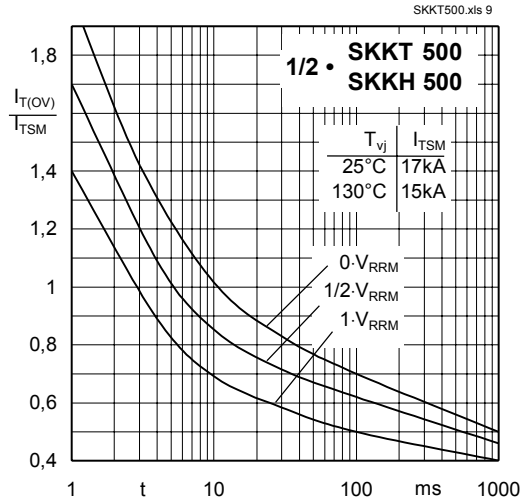


Fig. 9 Surge overload current vs. time

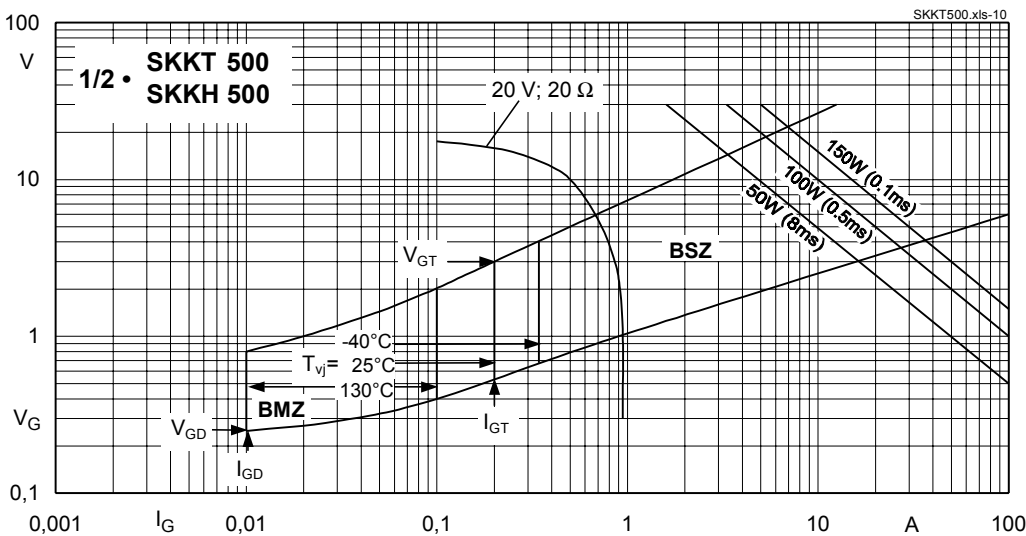
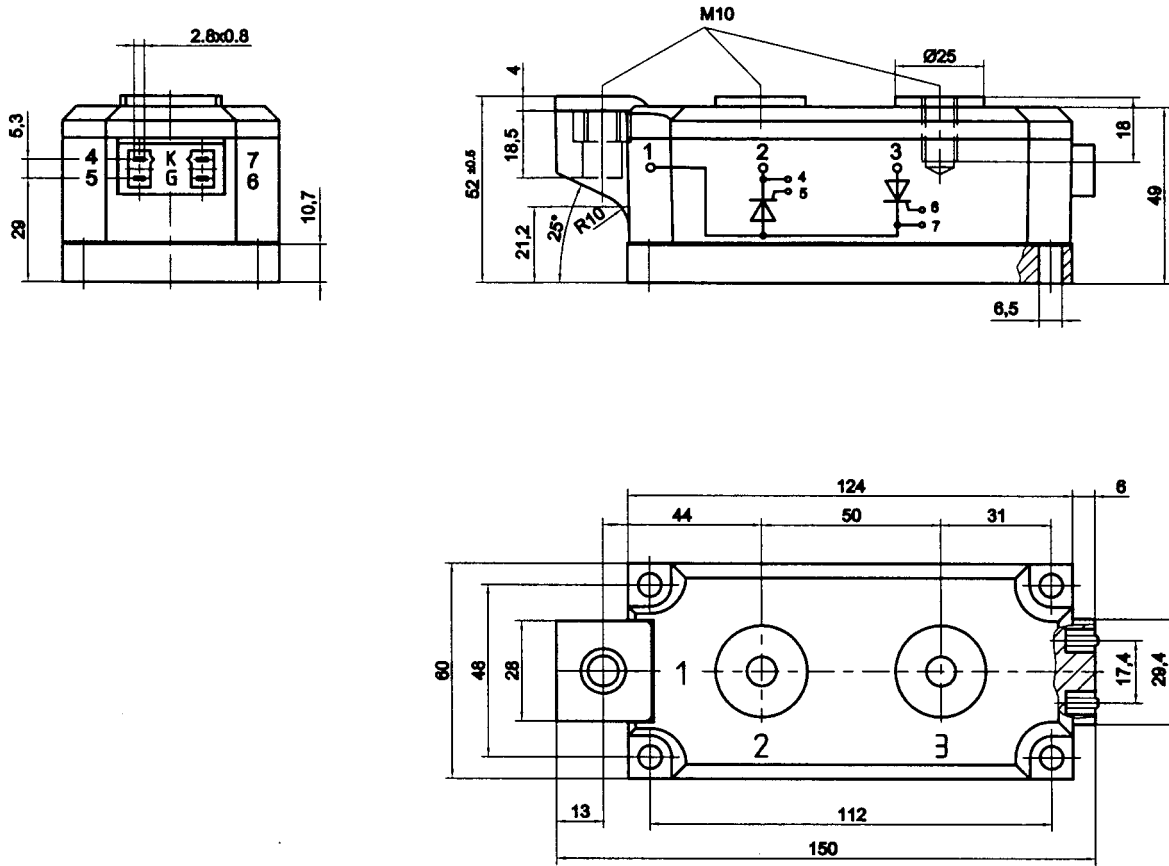


Fig. 10 Gate trigger characteristics

# SKKT 500, SKKH 500

## SKKT 500

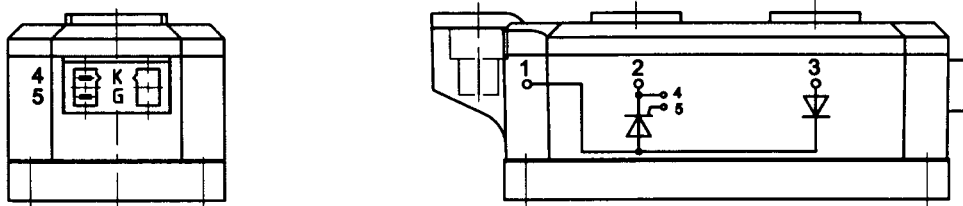
Case A 60 a  
SEMIPACK® 5



Dimensions in mm

## SKKH 500

Case A 66 a



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